■ Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V	-	-	1	μA
		V_{DS}=100V, V_{GS}=0V, Tj=150℃	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	2	2.8	4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=65A	-	4.5	5.5	mΩ
		V_{GS}=10V, I_D=20A	-	4.5	5.5	
Diode Forward Voltage	V_{SD}	I_S=65A, V_{GS}=0V	-	0.9	1.2	V
Gate resistance	R_G	f=1MHz, Open drain	-	0.8	-	Ω
Maximum Body-Diode Continuous Current	I_S		-	-	130	A
Dynamic Parameters						

Input Capacitance C_{iss}

V

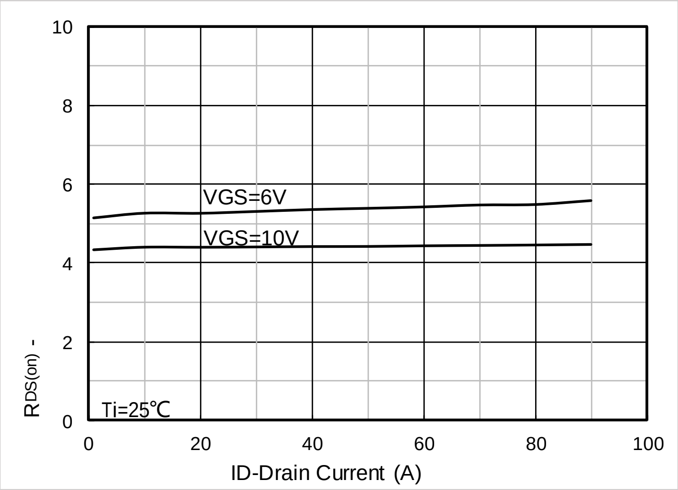

Figure7. RDS(on) VS Drain Current

Figure8. Forward characteristics of reverse diode

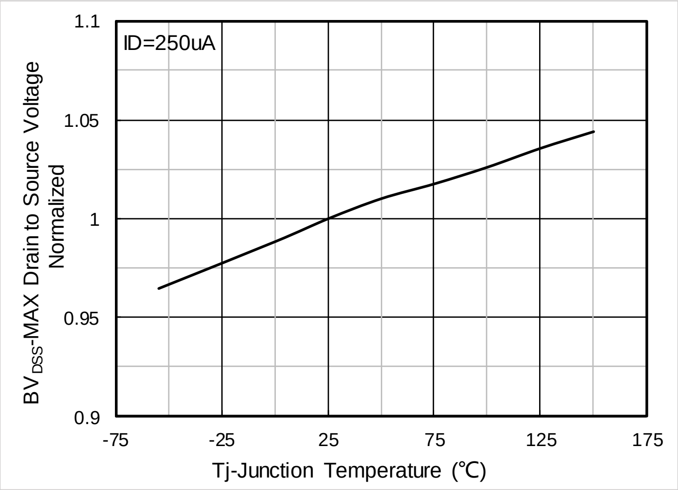

Figure9. Normalized breakdown voltage

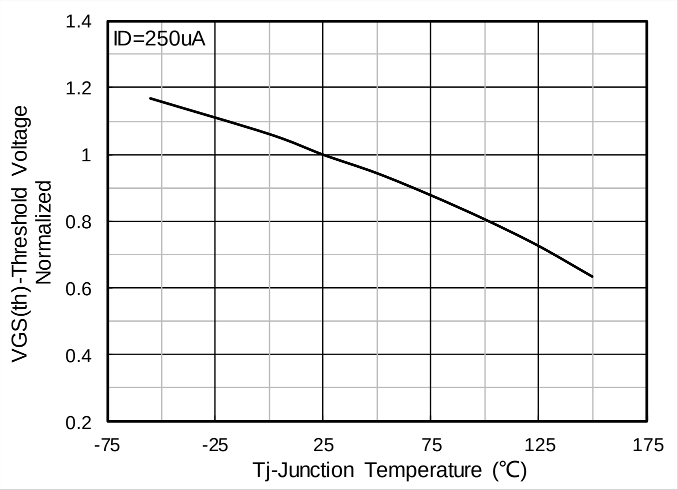

Figure10. Normalized Threshold voltage

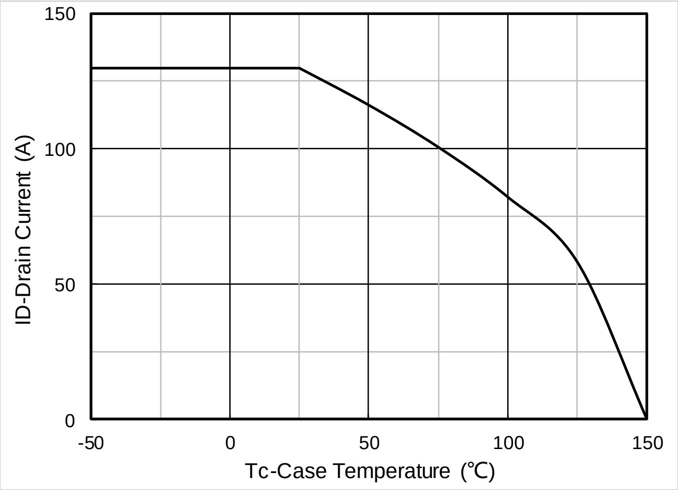

Figure11. Current dissipation

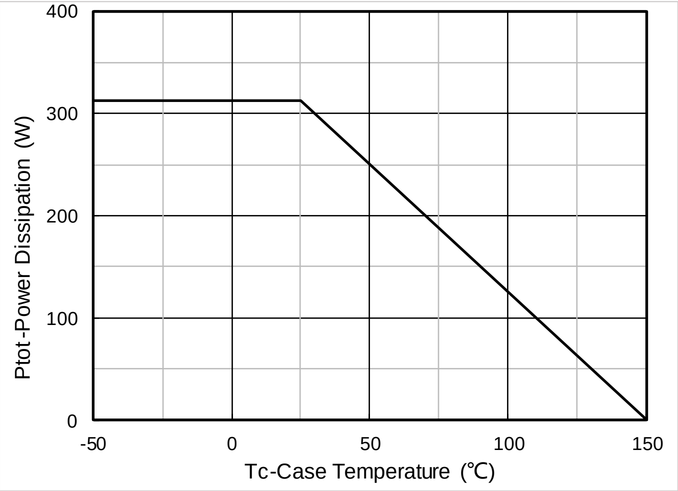

Figure12. Power dissipation

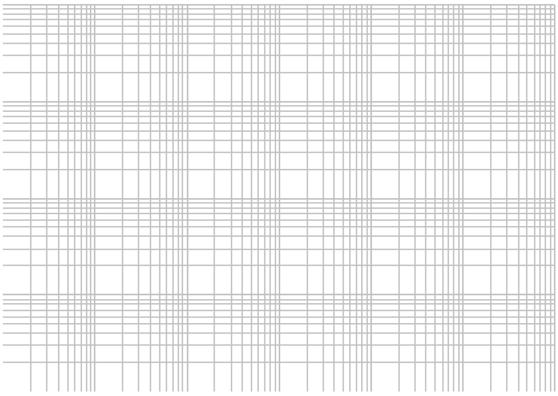

Figure13. Maximum Transient Thermal Impedance

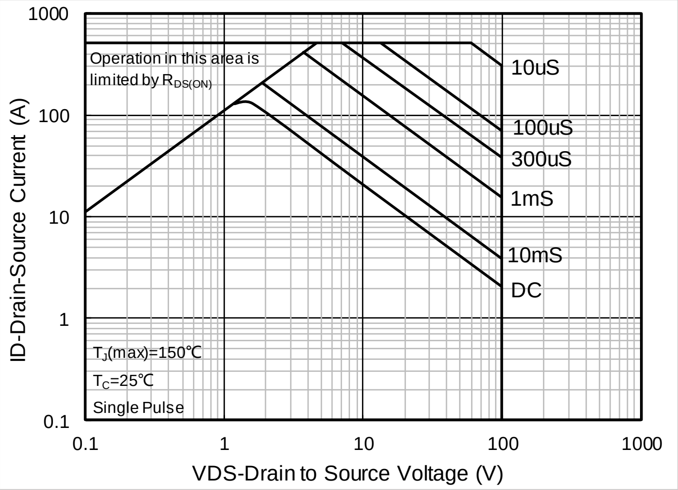

Figure14. Safe Operation Area

■ TO-220AB-D Package information

Disclaimer

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